

Features

- Uses PingWei advanced PerfectMOS technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Excellent Low Ciss
- Qualified according to JEDEC criteria



100% DVDS Tested
100% Avalanche Tested

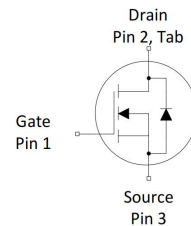
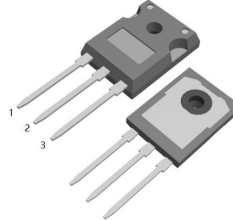
Applications

- PFC stages, hard switching PWM stages and resonant switching
- PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS

Product Summary

V_{DS}	900V
$R_{DS(on)}@10V$ typ	0.83Ω
I_D	9A

TO-247-3L



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
9N90Y	9N90Y	TO-247-3L	Tube	N/A	N/A	30pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	900	V
Continuous drain current	I_D	9	A
$T_C = 25^\circ\text{C}$ (Silicon limit)		6	A
$T_C = 100^\circ\text{C}$ (Silicon limit)			
Pulsed drain current ($T_C = 25^\circ\text{C}$)	$I_{D\ pulse}$	36	A
Avalanche energy, single pulse (L=10mH)	E_{AS}	551	mJ
Gate-Source voltage	V_{GS}	±30	V
Power dissipation	P_{tot}	250	W
$T_C = 25^\circ\text{C}$		2.5	
$T_a = 25^\circ\text{C}$			
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	°C
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	T_{sold}	260	°C

Thermal Resistance

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction – case.	RthJC	-	-	0.5	°C/W	-
Thermal resistance, junction - ambient(min. footprint)	RthJA	-	-	50	°C/W	-

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV _{DSS}	900	-	-	V	V _{GS} =0V, I _D =250uA
Gate threshold voltage	V _{GS(th)}	3	-	5	V	V _{DS} =V _{GS} , I _D =250uA
Zero gate voltage drain current	I _{DSS}	-	-	1 100	μA	V _{DS} =900V, V _{GS} =0V T _j =25°C T _j =150°C
Gate-source leakage current	I _{GSS}	-	-	±100	nA	V _{GS} =±30V, V _{DS} =0V
Drain-source on-state resistance	R _{DS(on)}	-	0.83	1.1	Ω	V _{GS} =10V, I _D =4.5A
Transconductance	g _{fs}	-	10	-	S	V _{DS} =5V, I _D =4.5A

Dynamic Characteristic

Input Capacitance	C _{iss}	-	2869	-	pF	V _{GS} =0V, V _{DS} =25V, f=1MHz
Output Capacitance	C _{oss}	-	221	-		
Reverse Transfer Capacitance	C _{rss}	-	5	-		
Gate Total Charge	Q _G	-	57	-	nC	V _{DS} =450V, I _D =4.5A , V _{GS} =10V
Gate-Source charge	Q _{gs}	-	17	-		
Gate-Drain charge	Q _{gd}	-	21	-		
Turn-on delay time	t _{d(on)}	-	18	-	ns	V _{GS} =10V, V _{DD} =400V, R _{G_ext} =2.5Ω, I _D =2.67A
Rise time	t _r	-	15	-		
Turn-off delay time	t _{d(off)}	-	48	-		
Fall time	t _f	-	38	-		
Gate resistance	R _G	-	1.1	-	Ω	V _{GS} =0V, V _{DS} =0V, f=1MHz



Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	-	1.5	V	$V_{GS}=0V, I_{SD}=4.5A$
Body Diode Continuous Forward Current	I_S	-	-	9	A	TC = 25°C
Body Diode Pulsed Current	I_S pulse	-	-	36	A	TC = 25°C

Typical Performance Characteristics

Fig 1: Output Characteristics

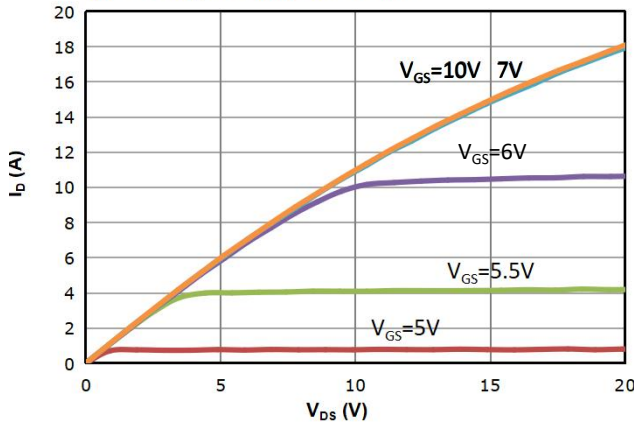


Fig 2: Transfer Characteristics

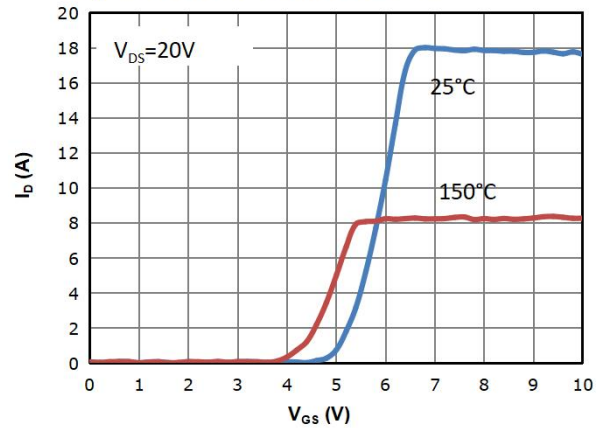


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

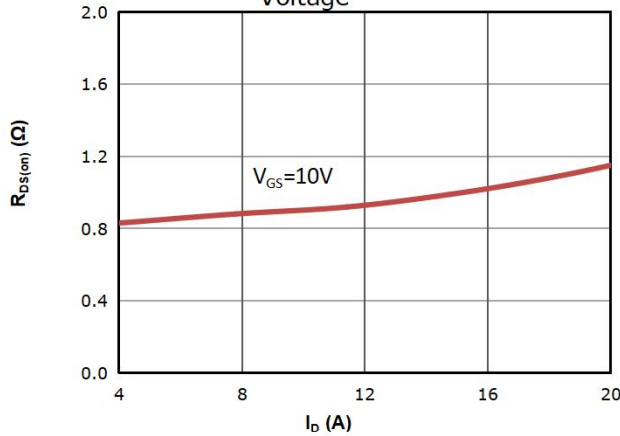


Fig 4: $R_{DS(on)}$ vs Gate Voltage

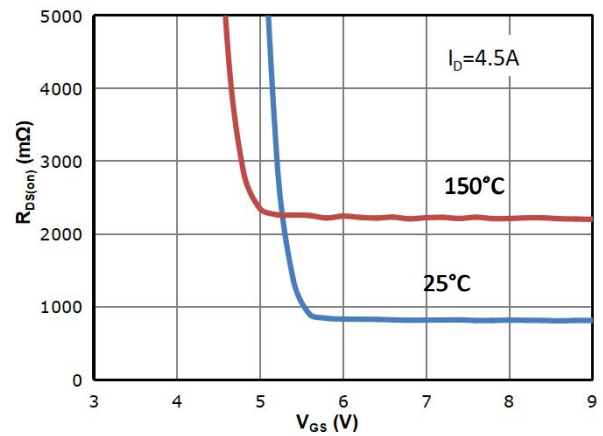


Fig 5: $R_{DS(on)}$ vs. Temperature

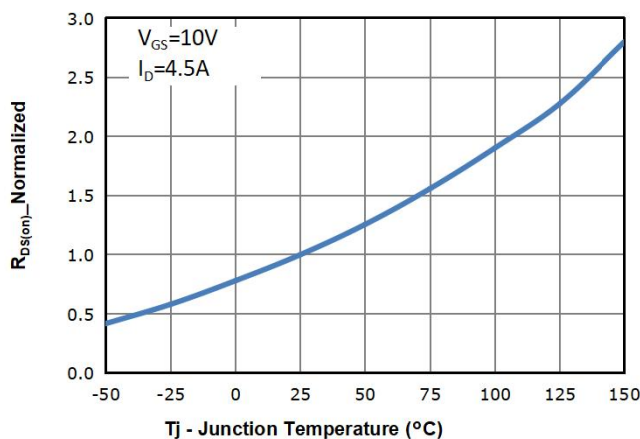


Fig 6: $V_{GS(th)}$ vs. Temperature

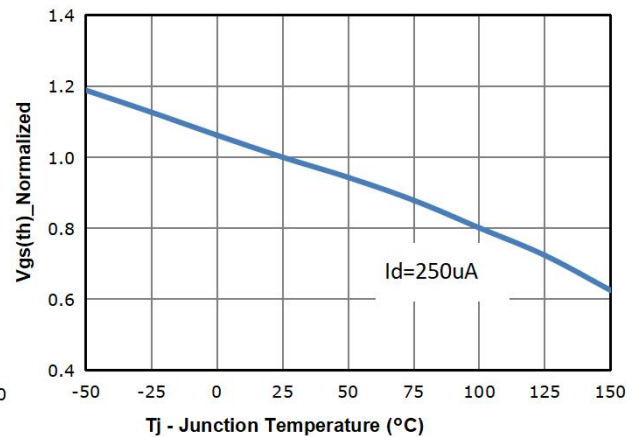


Fig 7: BVdss vs. Temperature

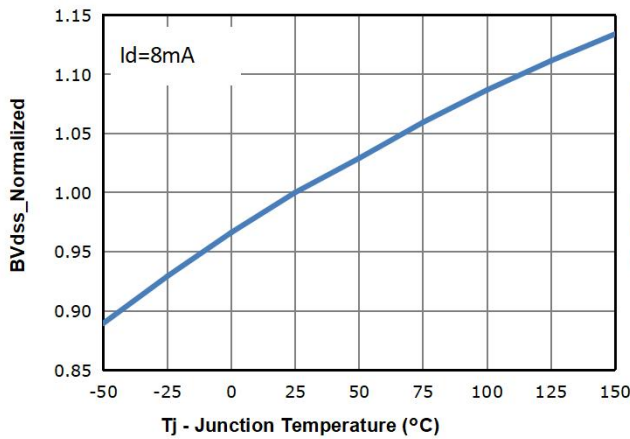


Fig 8: Capacitance Characteristics

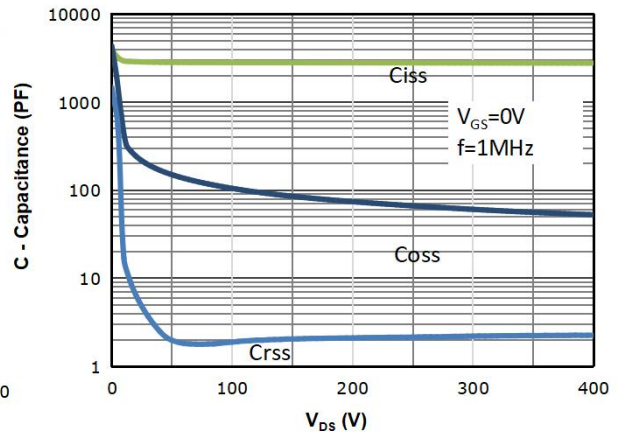


Fig 9: Gate Charge Characteristics

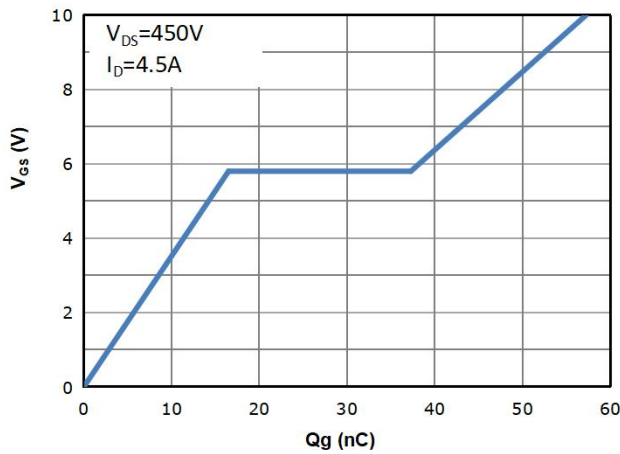


Fig 10: Body-diode Forward Characteristics

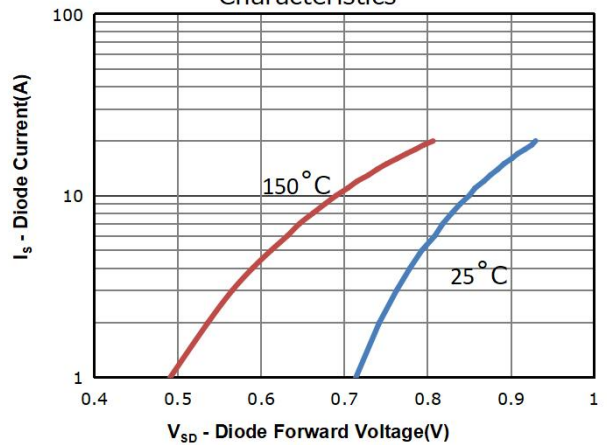


Fig 11: Power Dissipation

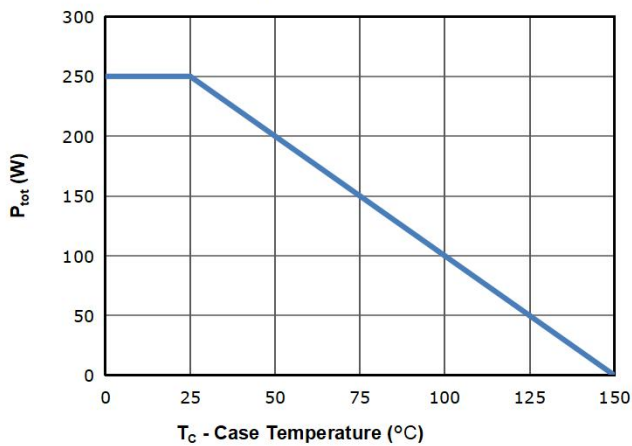


Fig 12: Drain Current Derating

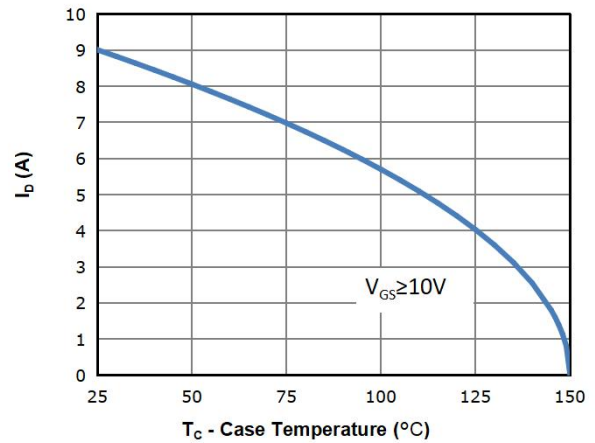


Fig 13: Safe Operating Area

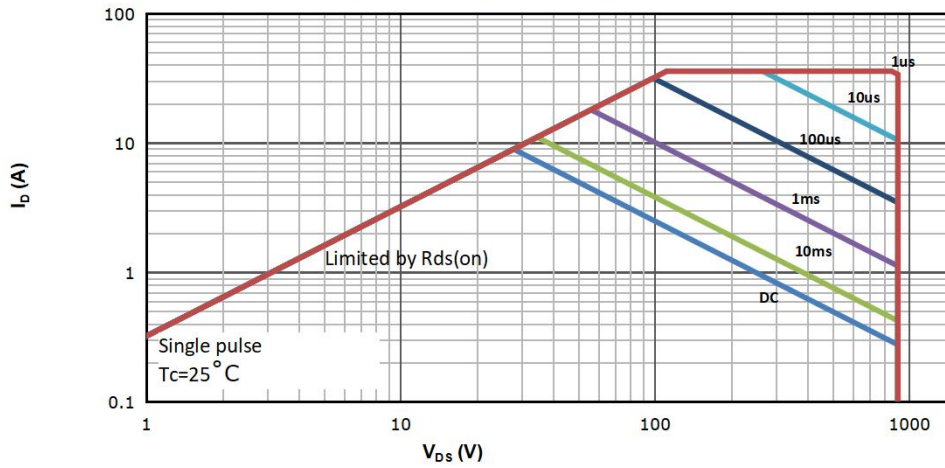
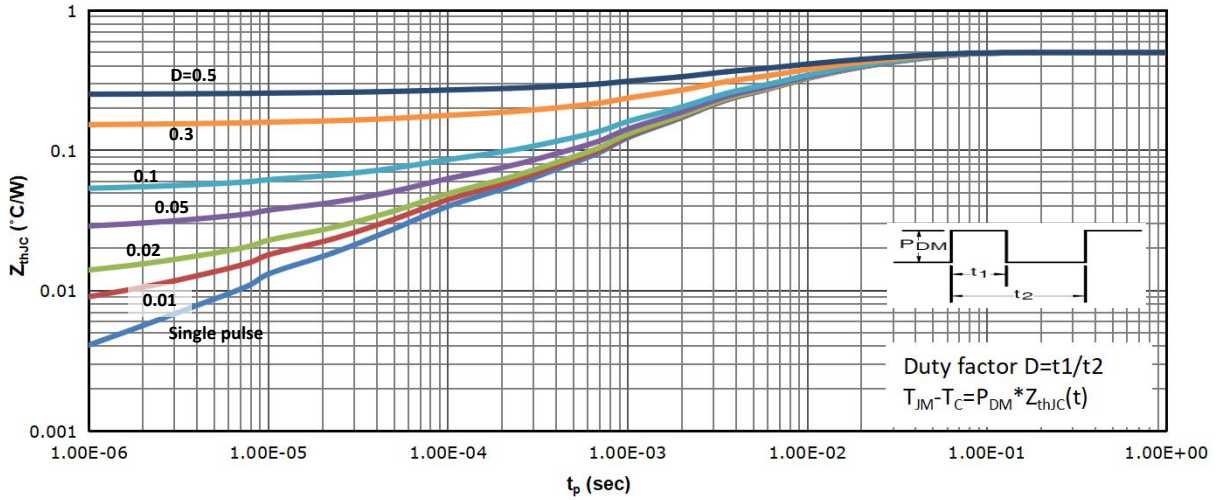
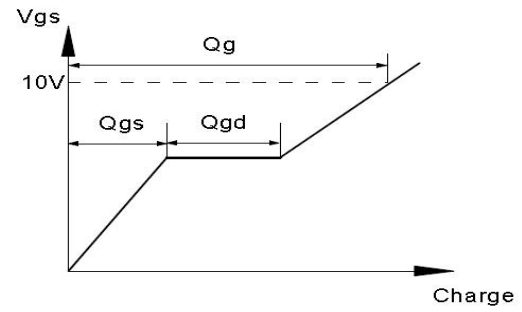
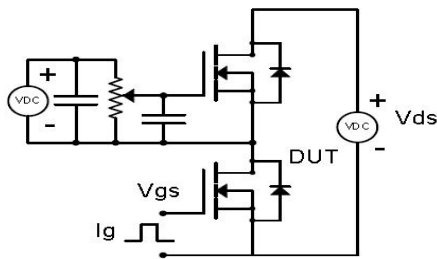


Fig 14: Max. Transient Thermal Impedance

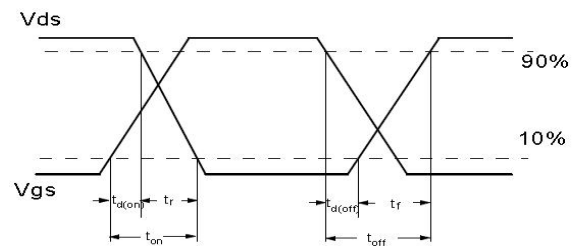
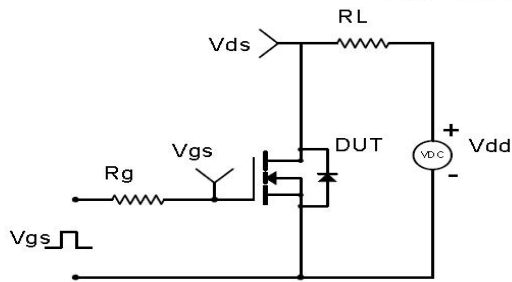


Test Circuit & Waveform

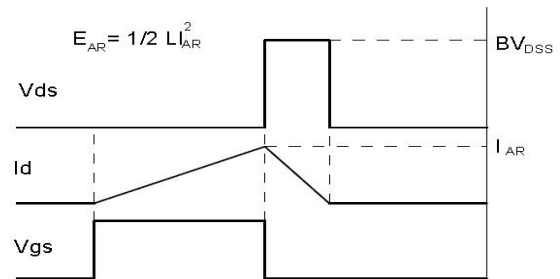
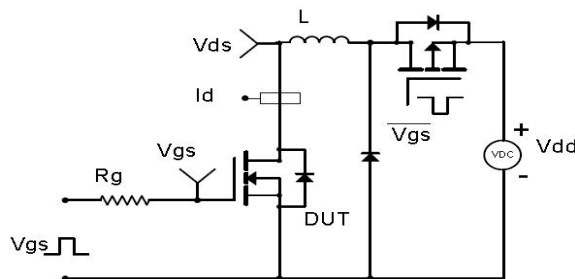
Gate Charge Test Circuit & Waveform



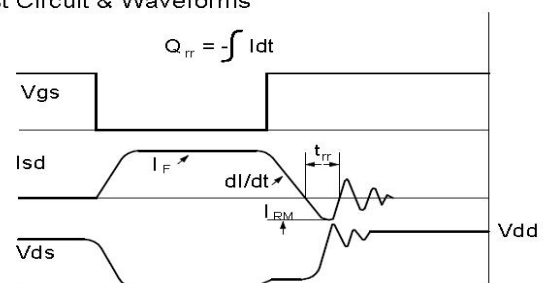
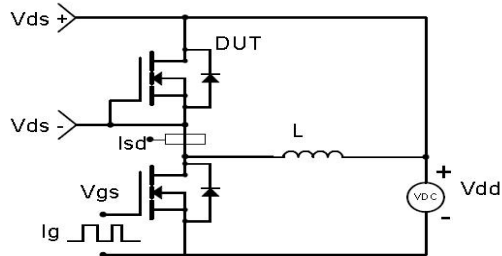
Resistive Switching Test Circuit & Waveforms



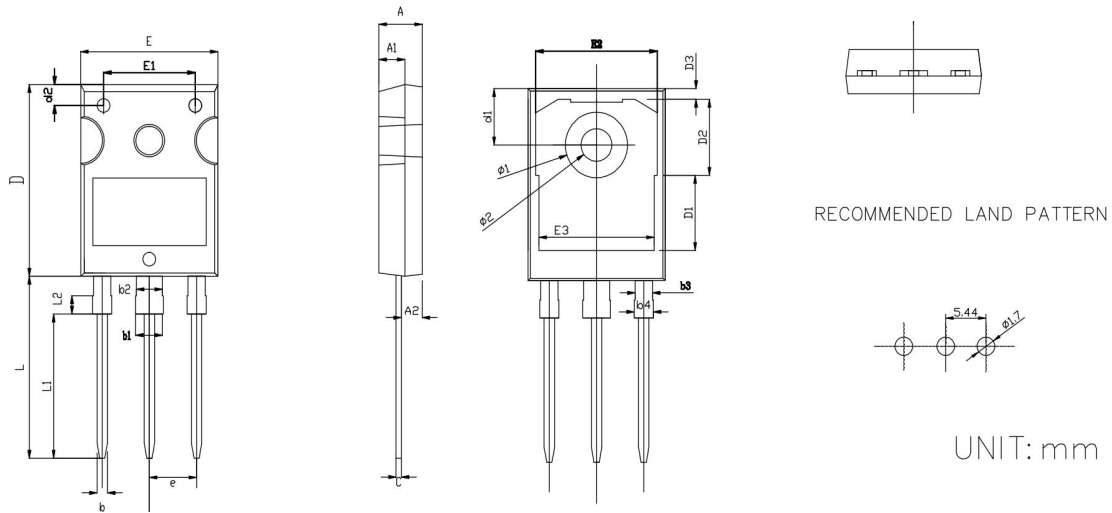
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: TO-247-3L



SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.20	0.189	0.205
A1	2.80	3.20	0.110	0.126
A2	2.26	2.56	0.089	0.101
b	1.10	1.30	0.043	0.051
b1	2.90	3.20	0.114	0.126
b2	2.90	3.10	0.114	0.122
b3	1.90	2.10	0.075	0.083
b4	2.00	2.20	0.079	0.087
c	0.50	0.70	0.020	0.028
D	20.80	21.20	0.819	0.835
D1	8.23		0.324	
D2	8.32		0.328	
D3	1.17		0.046	
d1	6.00	6.30	0.236	0.248
d2	2.20	2.40	0.087	0.094
E	15.60	16.00	0.614	0.630
E1	10.50		0.413	
E2	14.02		0.552	
E3	13.50		0.531	
e	5.34	5.54	0.210	0.218
L	19.72	20.12	0.776	0.792
L1	15.79		0.622	
L2	1.98		0.078	
φ1	7.10	7.30	0.280	0.287
φ2	3.50	3.70	0.138	0.146

Disclaimer

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

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